

N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
150	0.092 at V <sub>GS</sub> = 10 V	15		
	0.100 at V <sub>GS</sub> = 6 V	15		

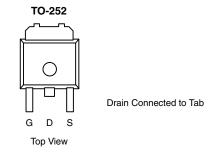
#### **FEATURES**

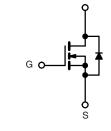
- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

· Primary Side Switch





N-Channel MOSFET

Ordering Information:	SUD15N15-95-E3 (Lead (Pb) free)

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	150		
Gate-Source Voltage			± 20	V	
Continuous Drain Current (T,I = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	15		
Continuous Drain Current (1 <sub>J</sub> = 175 °C)	T <sub>C</sub> = 125 °C		8.7		
Pulsed Drain Current		I <sub>DM</sub>	25	А	
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	15			
Avalanche Current	I <sub>AR</sub>	15			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	11.3	mJ	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	62 <sup>b</sup>	w	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	' D	2.7 <sup>a</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	- R <sub>thJA</sub>	16	20	°C/W	
Junction-to-Ambient*	Steady State		45	55		
Junction-to-Case		R <sub>thJC</sub>	2	2.4		

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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Parameter	Symbol	ol Test Conditions		Typ. <sup>a</sup>	Max.	Unit	
Static					l l		
Drain-Source Breakdown Voltage	$V_{DS}$ $V_{GS} = 0 \text{ V, } I_{D} = 250  \mu\text{A}$		150			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	25			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.077	0.095		
5 h	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C			0.190	0	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C			0.250	Ω	
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 10 A		0.081	0.100		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		25		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			900		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115			
Reverse Transfer Capacitance	C <sub>rss</sub>			70			
Total Gate Charge <sup>c</sup>	$Q_g$			20	25		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		5.5		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7			
Gate Resistance	R <sub>g</sub>		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55	nc	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		17	25	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	<sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				25	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15 A, dl/dt = 100 A/μs		55	85	ns	

#### Notes:

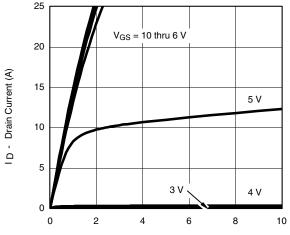
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

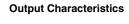


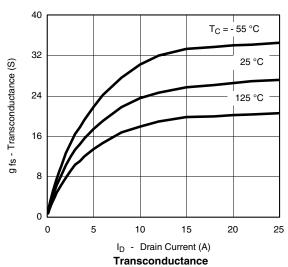
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### TYPICAL CHARACTERISTICS (25 °C unless noted)

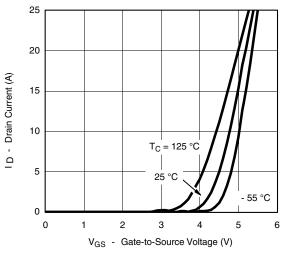


 $V_{DS}\,$  - Drain-to-Source Voltage (V)

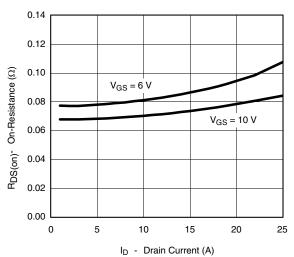




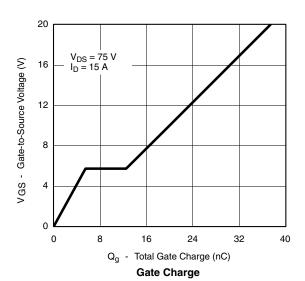
1500



**Transfer Characteristics** 



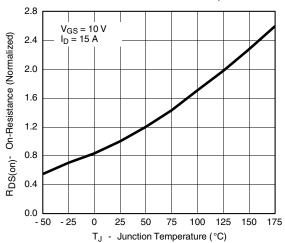
On-Resistance vs. Drain Current





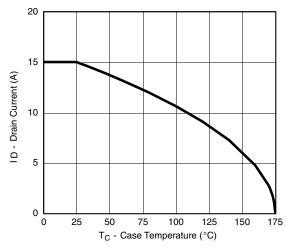
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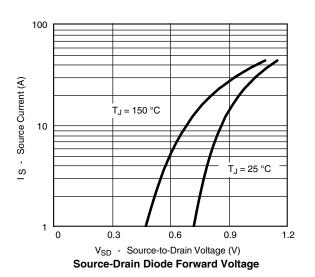


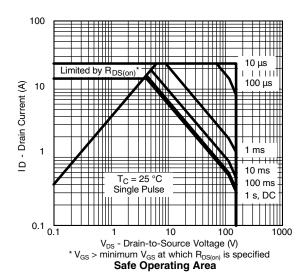
On-Resistance vs. Junction Temperature

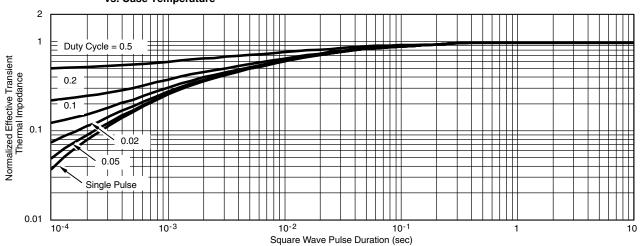
#### THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



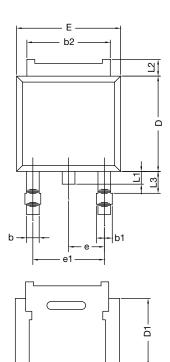


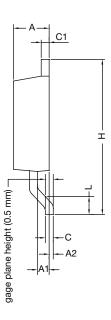


Normalized Thermal Transient Impedance, Junction-to-Case

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#### **TO-252AA CASE OUTLINE**





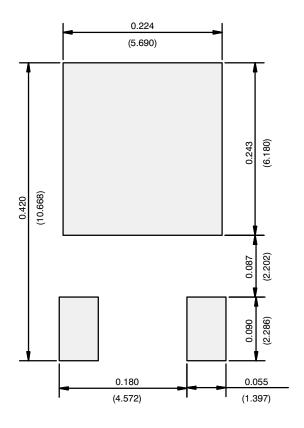
	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

#### Note

• Dimension L3 is for reference only.

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### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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